

Amendment to Claims

09/756,997

IN THE CLAIMS

Kindly amend claim 1, and cancel claims 2-5, all without prejudice, so that the claims are as follows:

1. (Currently Amended) A method for eliminating polymer blobs in a photoresist mask formed at the surface of a semiconductor wafer, comprising the steps of:

providing a semiconductor wafer having a photoresist layer formed thereon;

exposing, baking and developing the photoresist layer to produce a patterned photoresist mask; and

heating the wafer for a time sufficient to reach a temperature in a 100-400°C range and without cooling it, and then rinsing the wafer with deionized water at a temperature equal to or higher than the room temperature; wherein the semiconductor wafer comprises silicon, said step of heating the silicon wafer includes a step of post-development bake performed after said development step, the silicon wafer is immediately rinsed after said bake step, and the bake temperature is about 140°.

2. (Canceled)

3. (Canceled)

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4. (Canceled)

5. (Canceled)

6. (Canceled)

7. (Canceled)

8. (Canceled)

9. (Canceled)

10. (Canceled)

11. (Canceled)

12. (Canceled)

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